

ABSTRACT

EPITAXIAL GROWTH APPARATUS

An epitaxial growth apparatus is provided having an improved growing speed. This epitaxial growth apparatus is provided with: a reaction chamber that is demarcated by means of a substrate placing section having a substrate placed thereon, a ceiling plate having light permeability, and sidewall sections; a heating means, which is disposed outside of the reaction chamber, and which heats the substrate through the ceiling plate, said substrate being placed in the reaction chamber; and a reaction gas introducing means, which introduces into the reaction chamber a reaction gas in parallel to the horizontal direction of the substrate. The distance between the center of the ceiling plate and the substrate placing section is less than 10 mm.

FIG.1